

## ABSTRACT OF THE DISCLOSURE

An electroplating solution comprising copper ions and a complexing agent for the copper ions and has a pH in the 5 range of 4 to 10. The electroplating solution of the present invention makes it possible to fill trenches or via holes on silicon wafers for providing copper wiring with copper in a defect-free manner by preventing the seed layer from dissolving in the plating solution.

the *Journal of the Royal Society of Medicine* and the *Journal of Clinical Pathology*.